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SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246065US2S	SERIAL NO. 10/722,514		
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Kentaro NAKAJIMA, et al.			
				FILING DATE November 28, 2003	GROUP 2818		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
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	AD						
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	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>TH</i>	AW	Roy SCHEUERLEIN et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", ISSCC Digest of Technical Papers, 2000, Session 7, Paper TA 7.2					
<i>TH</i>	AX	Masashige SATO et al., "Spin-Valve-Like Properties and Annealing Effect in Ferromagnetic Tunnel Junctions", IEEE Transactions on Magnetics, 1997, Vol. 33, No. 5, pp. 3553-3555					
<i>TH</i>	AY	Masashige SATO et al., "Spin-Valve-Like Properties of Ferromagnetic Tunnel Junctions", Jpn. J. Appl. Phys., 1997, Vol. 36, Part 2, pp. 200-201					
<i>TH</i>	AZ	Koichi INOMATA et al., "Spin-Dependent Tunneling between a Soft Ferromagnetic Layer and Hard Magnetic Nanosize Particles", Jpn. J. Appl. Phys., 1997, Vol. 36, Part 2, pp. 1380-1383					<input type="checkbox"/> Additional References sheet(s) attached
Examiner <i>TU-SUE HO</i>					Date Considered <i>Feb. 2005</i>		

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.